

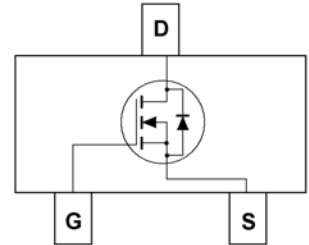
## N-Channel Enhancement Mode MOSFET

### Feature

- 30V/4.5A,  $R_{DS(ON)} = 35\text{m}\Omega(\text{MAX}) @V_{GS} = 10\text{V}$ .  
 $R_{DS(ON)} = 40\text{m}\Omega(\text{MAX}) @V_{GS} = 4.5\text{V}$ .  
 $R_{DS(ON)} = 55\text{m}\Omega(\text{MAX}) @V_{GS} = 2.5\text{V}$ .
- Super High dense cell design for extremely low  $R_{DS(ON)}$ .
- Reliable and Rugged.
- SOT-23 for Surface Mount Package.



SOT-23



### Applications

- Power Management  
 Portable Equipment and Battery Powered Systems.

### Absolute Maximum Ratings TA=25°C Unless Otherwise noted

| Parameter                | Symbol   | Limit    | Units |
|--------------------------|----------|----------|-------|
| Drain-Source Voltage     | $V_{DS}$ | 30       | V     |
| Gate-Source Voltage      | $V_{GS}$ | $\pm 12$ | V     |
| Drain Current-Continuous | $I_D$    | 4.5      | A     |

### Electrical Characteristics TA=25°C Unless Otherwise noted

| Parameter   | Symbol       | Test Conditions                        | Min | Typ. | Max  | Units            |
|---|--------------|--|-----|------|------|------------------|
| <b>Off Characteristics</b>                                    |              |  |     |      |      |                  |
| Drain to Source Breakdown Voltage                             | BVDSS        | $V_{GS}=0\text{V}, I_D=250\mu\text{A}$ | 30  | -    | -    | V                |
| Zero-Gate Voltage Drain Current                               | $I_{DSS}$    | $V_{DS}=30\text{V}, V_{GS}=0\text{V}$  | -   | -    | 1    | $\mu\text{A}$    |
| Gate Body Leakage Current, Forward                            | $I_{GSSF}$   | $V_{GS}=12\text{V}, V_{DS}=0\text{V}$  | -   | -    | 100  | nA               |
| Gate Body Leakage Current, Reverse                            | $I_{GSSR}$   | $V_{GS}=-12\text{V}, V_{DS}=0\text{V}$ | -   | -    | -100 | nA               |
| <b>On Characteristics</b>                                     |              |  |     |      |      |                  |
| Gate Threshold Voltage  | $V_{GS(th)}$ | $V_{GS}=V_{DS}, I_D=250\mu\text{A}$    | 0.6 | -    | 1.5  | V                |
| Static Drain-source On-Resistance                             | $R_{DS(ON)}$ | $V_{GS}=10\text{V}, I_D=5.8\text{A}$   | -   | 30   | 35   | $\text{m}\Omega$ |
|   |              | $V_{GS}=4.5\text{V}, I_D=5\text{A}$    | -   | 33   | 40   | $\text{m}\Omega$ |
|   |              | $V_{GS}=2.5\text{V}, I_D=4\text{A}$    | -   | 45   | 55   | $\text{m}\Omega$ |
| <b>Drain-Source Diode Characteristics and Maximum Ratings</b> |              |  |     |      |      |                  |
| Drain-Source Diode Forward Voltage                            | VSD          | $V_{GS}=0\text{V}, I_S=1.25\text{A}$   |     |      | 1.2  | V                |

| Dynamic      |                     |   |     |    |    |
|--------------|---------------------|---|-----|----|----|
| $Q_g$        | Total Gate Charge   | $V_{DS}=15V, V_{GS}=10V, I_D=2A$              | 8.5 | 12 | nC |
| $Q_{gs}$     | Gate-Source Charge  |   | 1.1 |    |    |
| $Q_{gd}$     | Gate-Drain Charge   |   | 1.8 |    |    |
| $t_{on}$     | Turn-on Time        | $V_{DD}=15V, I_D=2A, V_{GS}=10V, R_G=6\Omega$ |     | 40 | ns |
| $t_{d(ON)}$  | Turn-on Delay time  |   | 11  |    |    |
| $t_r$        | Turn-on Rise Time   |   | 17  |    |    |
| $T_{d(off)}$ | Turn-off Delay Time |   | 37  |    |    |
| $t_f$        | Turn-off Fall Time  |   | 20  |    |    |
| $t_{off}$    | Turn-off Time       |   |     | 60 |    |

## Typical Characteristics

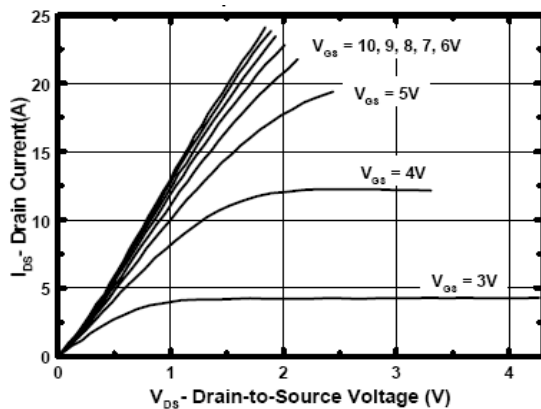


Figure 1. Output Characteristics

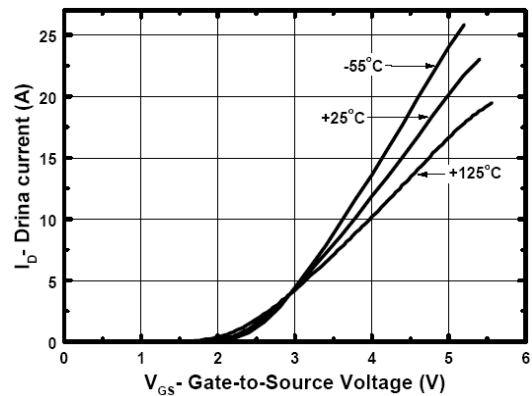


Figure 2. Transfer Characteristics

## Typical Characteristics

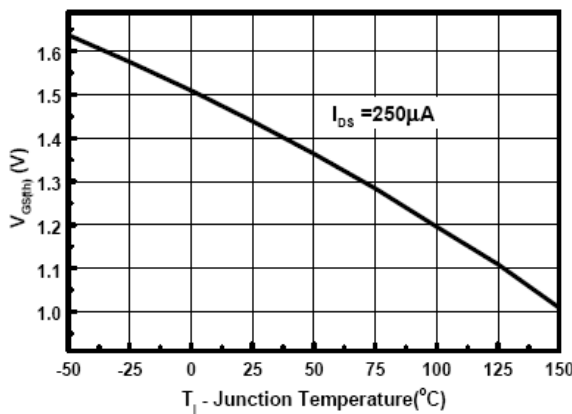


Figure 3. Gate Threshold Variation with Temperature

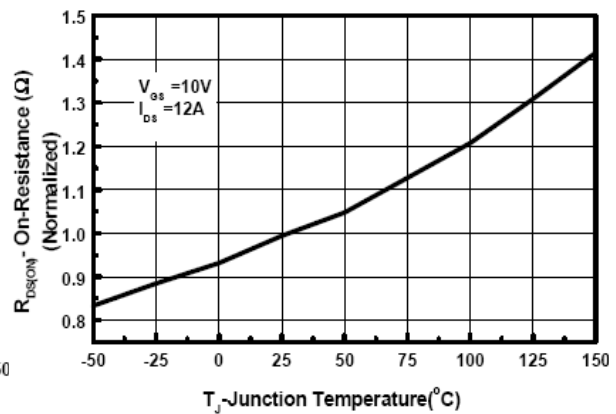


Figure 4. On-Resistance Variation with Temperature

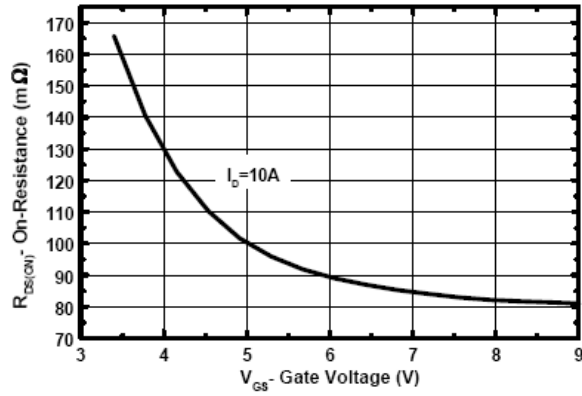


Figure 5. On-Resistance vs. Gate-to-Source Voltage

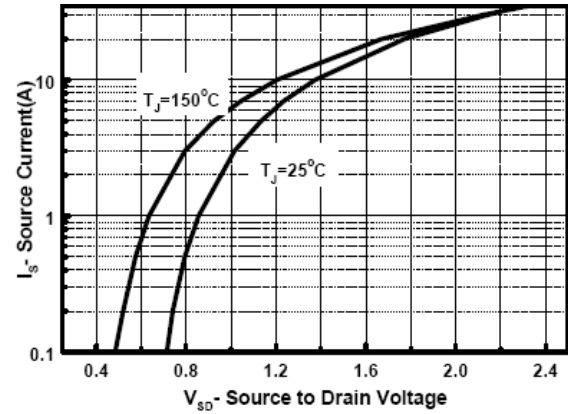


Figure 6. Source-Drain Diode Forward

## Package Outline Dimensions (UNIT: mm)

### SOT-23

